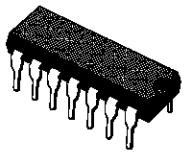
SGS-THOMSON MICROELECTRONICS

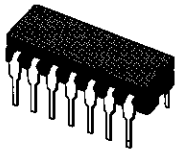
HCC40106B
HCF40106B

HEX SCHMITT TRIGGERS

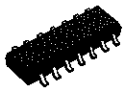
- SCHMITT-TRIGGER ACTION WITH NO EXTERNAL COMPONENTS
- HYSTERESIS VOLTAGE (TYP.) 0.9V AT V_{DD} = 5V, 2.3V AT V_{DD} = 10V AND 3.5V AT V_{DD} = 15V
- NOISE IMMUNITY GREATER THAN 50%
- NO LIMIT ON INPUT RISE AND FALL TIME
- LOW V_{DD} TO V_{SS} CURRENT DURING SLOW INPUT RAMP
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



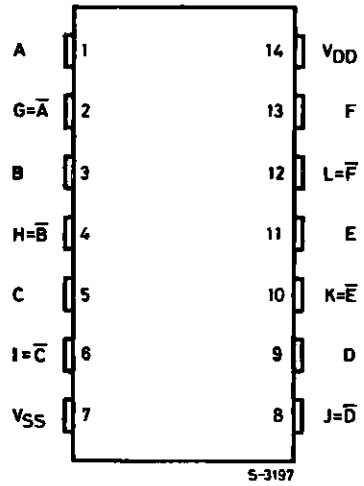
M1
(Micro Package)

C1
(Plastic Chip Carrier)

ORDER CODES :

HCC40106BF	HCF40106BM1
HCF40106BEY	HCF40106BC1

PIN CONNECTIONS

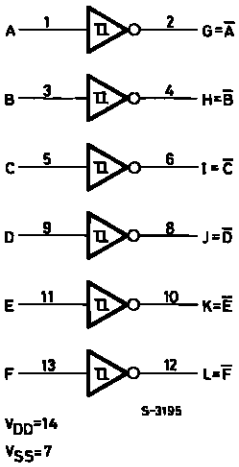


DESCRIPTION

The **HCC40106B** (extended temperature range) and **HCF40106B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF40106B** consists of six Schmitt-trigger circuits. Each circuit functions as an inverter with Schmitt-trigger action on the input. The trigger switches at different points for positive and negative-going signals. The difference between the positive-going voltage (V_P) and the negative-going voltage (V_N) is defined as hysteresis voltage (V_H).

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

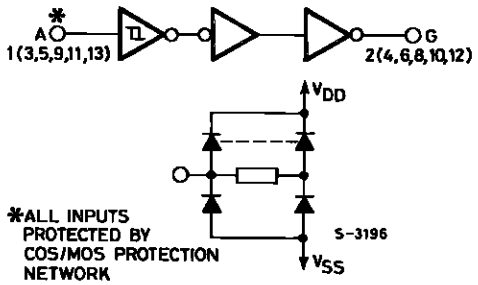
Symbol	Parameter	Value	Unit
V_{DD}*	Supply Voltage : **HCC** Types **HCF** Types	– 0.5 to + 20 – 0.5 to + 18	V V
V_i	Input Voltage	– 0.5 to V_{DD} + 0.5	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : **HCC** Types **HCF** Types	– 55 to + 125 – 40 to + 85	°C °C
T_{stg}	Storage Temperature	– 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : **HCC** Types **HCF** Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : **HCC** Types **HCF** Types	– 55 to + 125 – 40 to + 85	°C °C

LOGIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value							Unit
			V_I (V)	V_O (V)	$\|I_O\|$ (µA)	V_{DD} (V)	T_{Low}*		25°C			T_{High}*		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I_L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	µA
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V_{OH}	Output High Voltage		0/ 5		< 1	5	4.95		4.95			4.95		V
			0/10		< 1	10	9.95		9.95			9.95		
			0/15		< 1	15	14.95		14.95			14.95		
V_{OL}	Output Low Voltage		5/10		< 1	5		0.05			0.05		0.05	V
			10/0		< 1	10		0.05			0.05		0.05	
			15/0		< 1	15		0.05			0.05		0.05	
V_P	Positive Trigger Threshold Voltage					5	2.2	3.6	2.2	2.9	3.6	2.2	3.6	V
						10	4.6	7.1	4.6	5.9	7.1	4.6	7.1	
						15	6.8	10.8	6.8	8.8	10.8	6.8	10.8	
V_N	Negative Trigger Threshold Voltage					5	0.9	2.8	0.9	1.9	2.8	0.9	2.8	V
						10	2.5	5.2	2.5	3.9	5.2	2.5	5.2	
						15	4	7.4	4	5.8	7.4	4	7.4	
V_H	Hysteresis Voltage					5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	V
						10	1.2	3.4	1.2	2.3	3.4	1.2	3.4	
						15	1.6	5	1.6	3.5	5	1.6		

* T_{Low}= – 55°C for **HCC** device : – 40°C for **HCF** device.
* T_{High}= + 125°C for **HCC** device : + 85°C for **HCF** device.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value							Unit
			V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T_{Low}*		25°C			T_{High}*		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I_{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	– 2		– 1.6	– 3.2		– 1.15		mA
			0/ 5	4.6		5	– 0.64		– 0.51	– 1		– 0.36		
			0/10	9.5		10	– 1.6		– 1.3	– 2.6		– 0.9		
			0/15	13.5		15	– 4.2		– 3.4	– 6.8		– 2.4		
		HCF Types	0/ 5	2.5		5	– 1.53		– 1.36	– 3.2		– 1.1		
			0/ 5	4.6		5	– 0.52		– 0.44	– 1		– 0.36		
			0/10	9.5		10	– 1.3		– 1.1	– 2.6		– 0.9		
			0/15	13.5		15	– 3.6		– 3.0	– 6.8		– 2.4		
I_{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.6		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.9		
I_{IH}, I_{IL}**	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μA
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C_I	Input Capacitance			Any Input						5	7.5			p

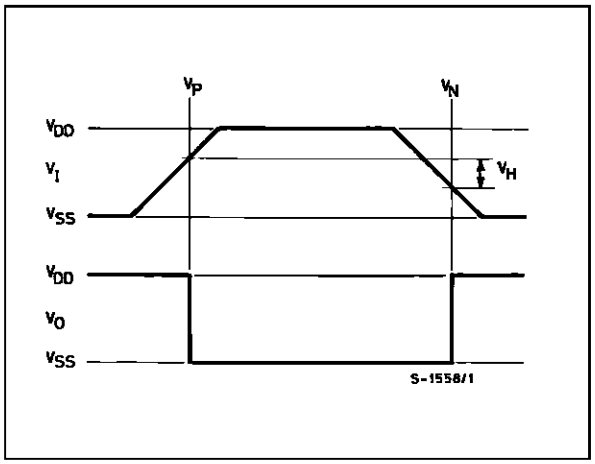
* T_{Low} = – 55°C for **HCC** device : – 40°C for **HCF** device.
* T_{High} = + 125°C for **HCC** device : + 85°C for **HCF** device.

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200kΩ, typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall time = 20ns)

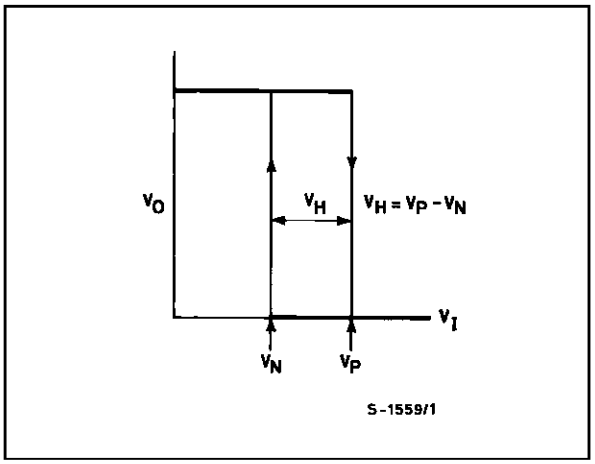
Symbol	Parameter	Test Conditions	Value				Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH}, t_{PHL}	Propagation Delay Time		5		140	280	ns
			10		70	140	
			15		60	120	
t_{THL}, t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

HYSTERESIS DEFINITION, CHARACTERISTICS AND TEST SETUP

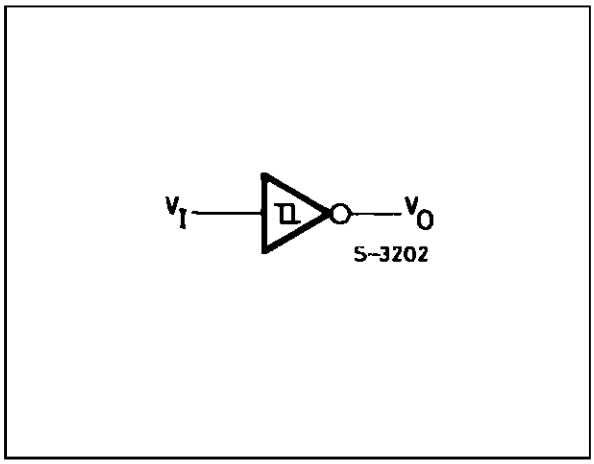
(a) Definition of V_P, V_N and V_H.



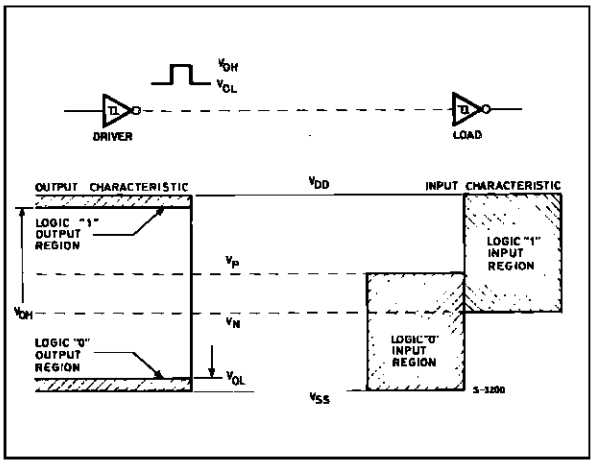
(b) Transfer Characteristic of 1 of 6 gates.



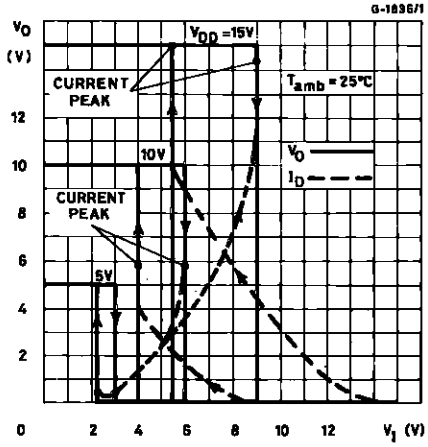
(c) Test Setup.

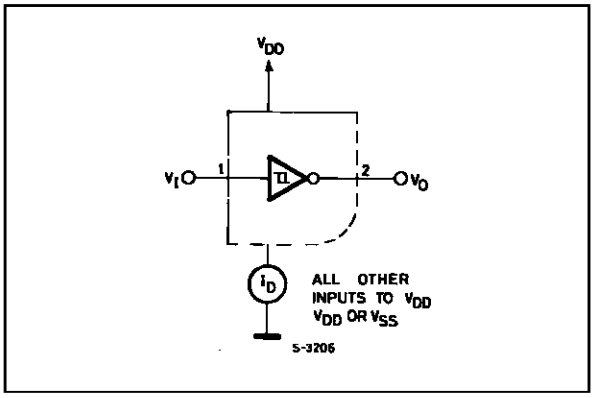


Input and Output Characteristics.



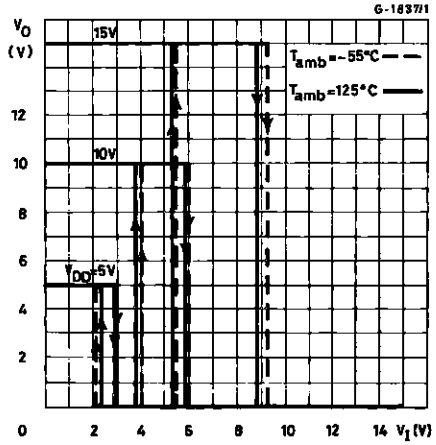
Typical Current Voltage Transfer Characteristics, and Test Circuit.

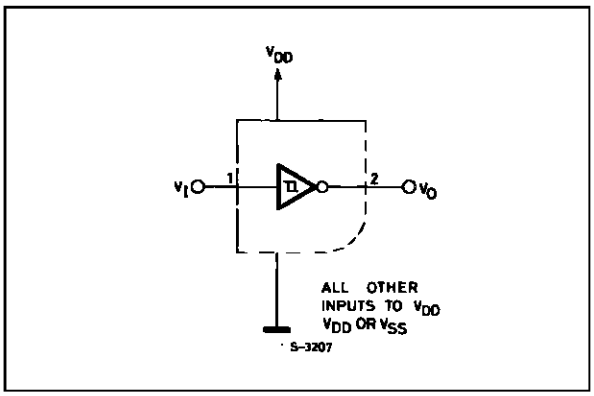




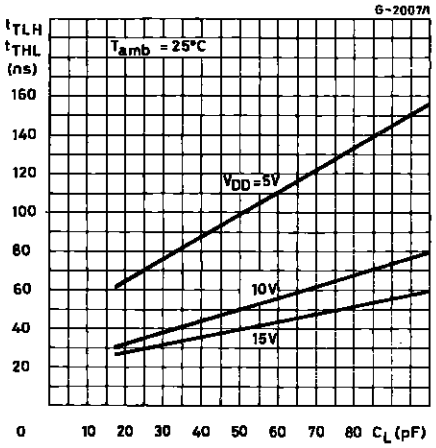
HYSTERESIS DEFINITION, CHARACTERISTICS AND TEST SETUP

Typical Voltage Transfer Characteristics vs. Temperature, and Test Circuit.

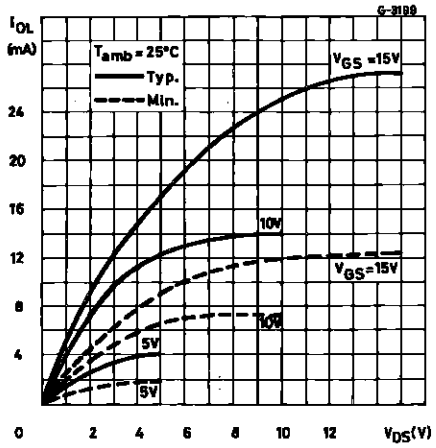




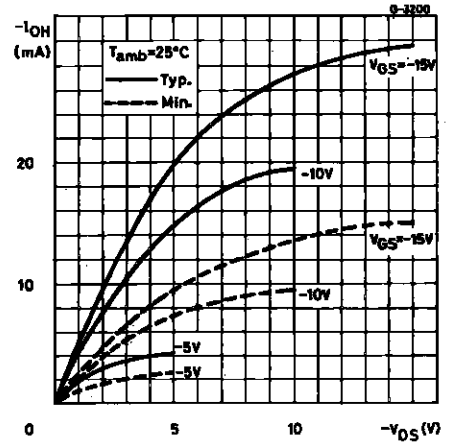
Typical Transition Time vs. Load Capacitance.



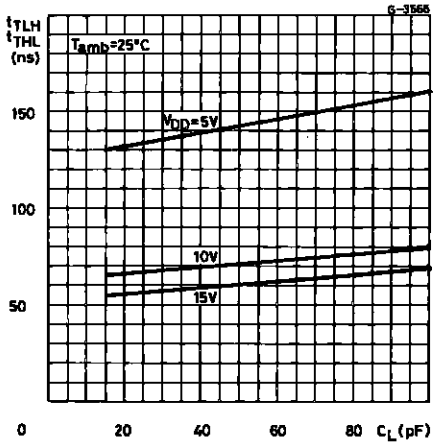
Output Low (sink) Current Characteristics.



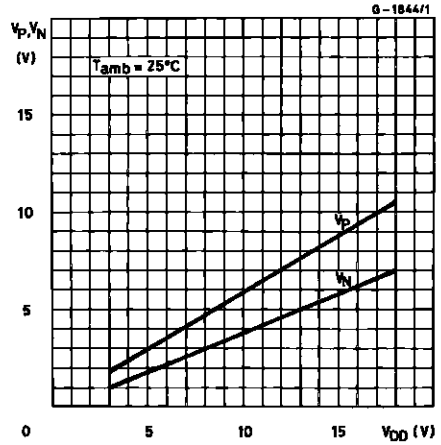
Output High (source) Current Characteristics.



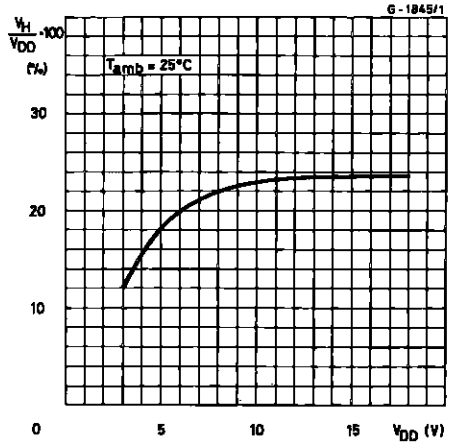
Typical Propagation Delay Time vs. Load Capacitance.



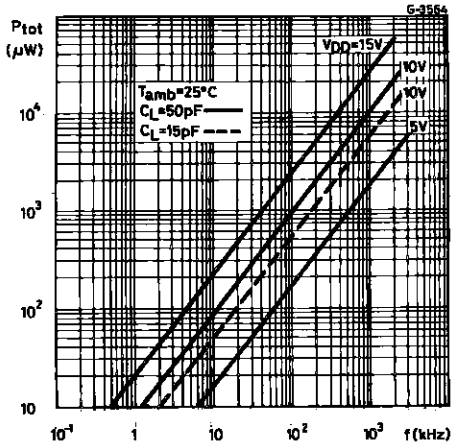
Typical Trigger Threshold Voltage vs. Supply Voltage .



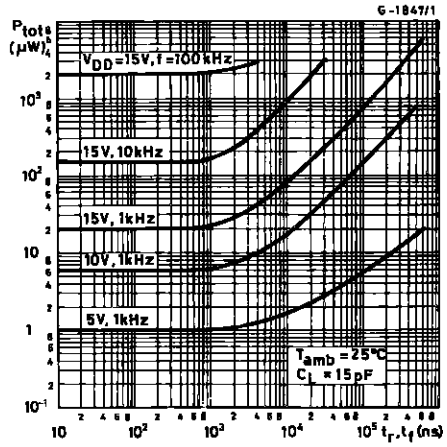
Typical per Cent Hysteresis vs. Supply Voltage.



Typical Power Dissipation per Trigger vs. Input Frequency.

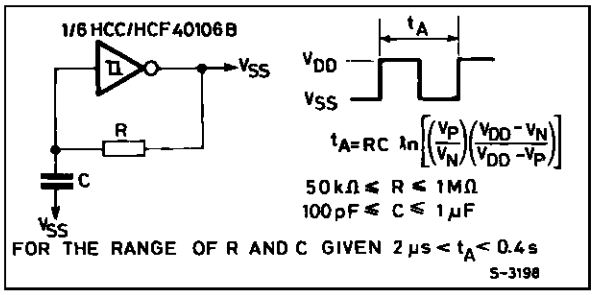


Typical Power Dissipation per Trigger vs. Input Frequency.

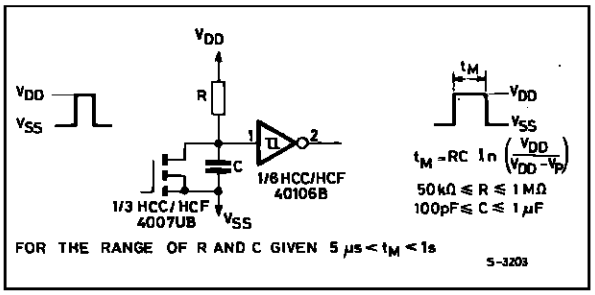


TYPICAL APPLICATIONS

ASTABLE MULTIVIBRATOR.

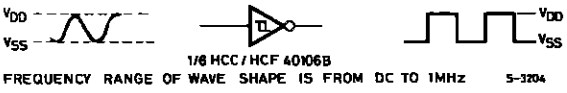


MONOSTABLE MULTIVIBRATOR.



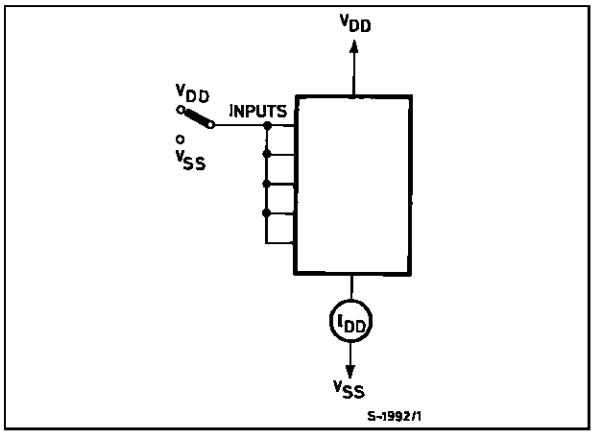
TYPICAL APPLICATIONS (continued)

WAVE SHAPER.

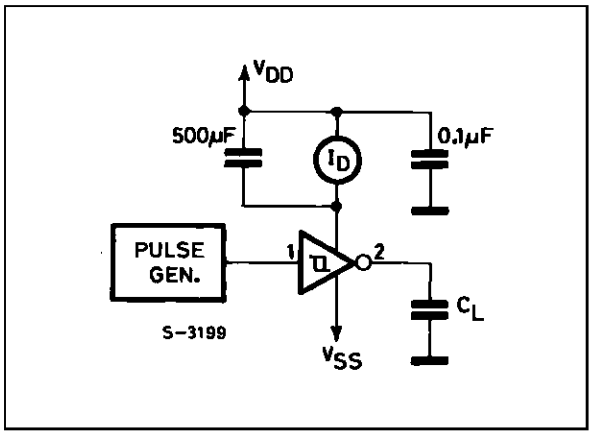


TEST CIRCUITS

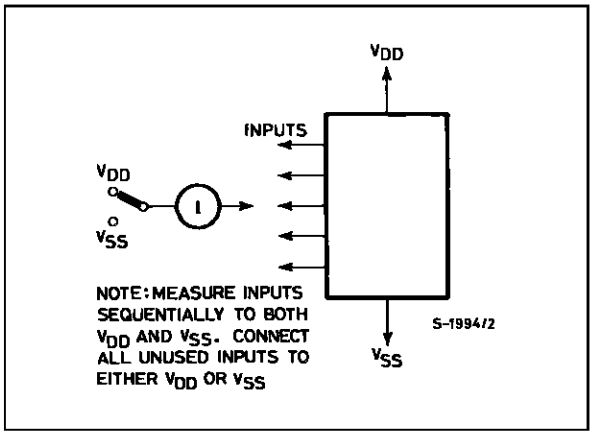
Quiescent Device Current.



Dynamic Power Dissipation.

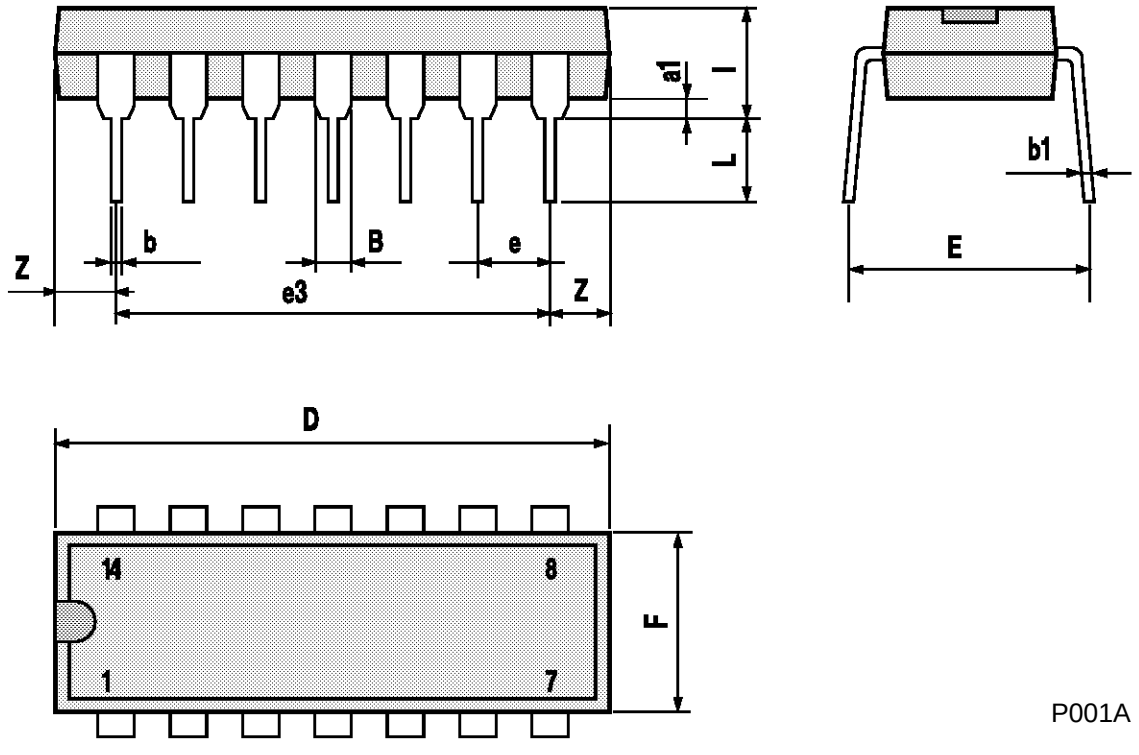


Input Current .



Plastic DIP14 MECHANICAL DATA

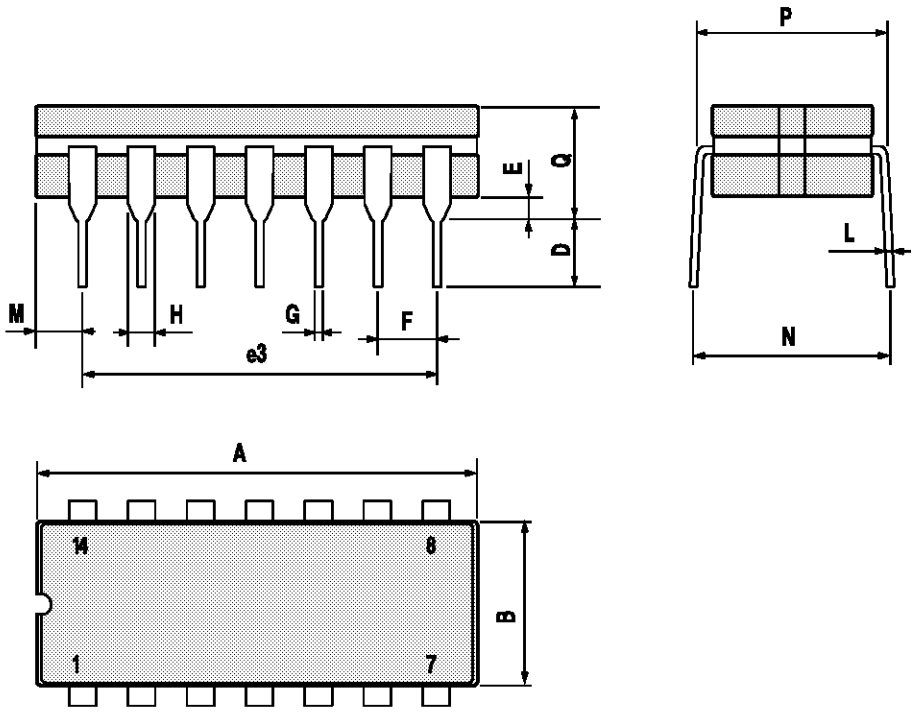
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

Ceramic DIP14/1 MECHANICAL DATA

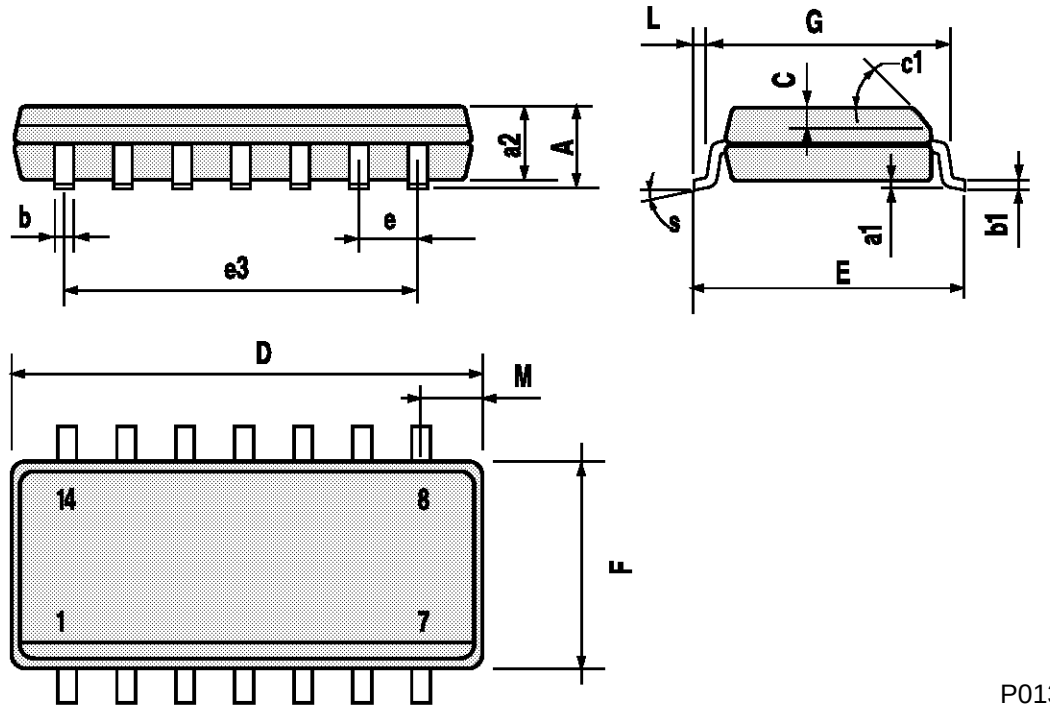
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

SO14 MECHANICAL DATA

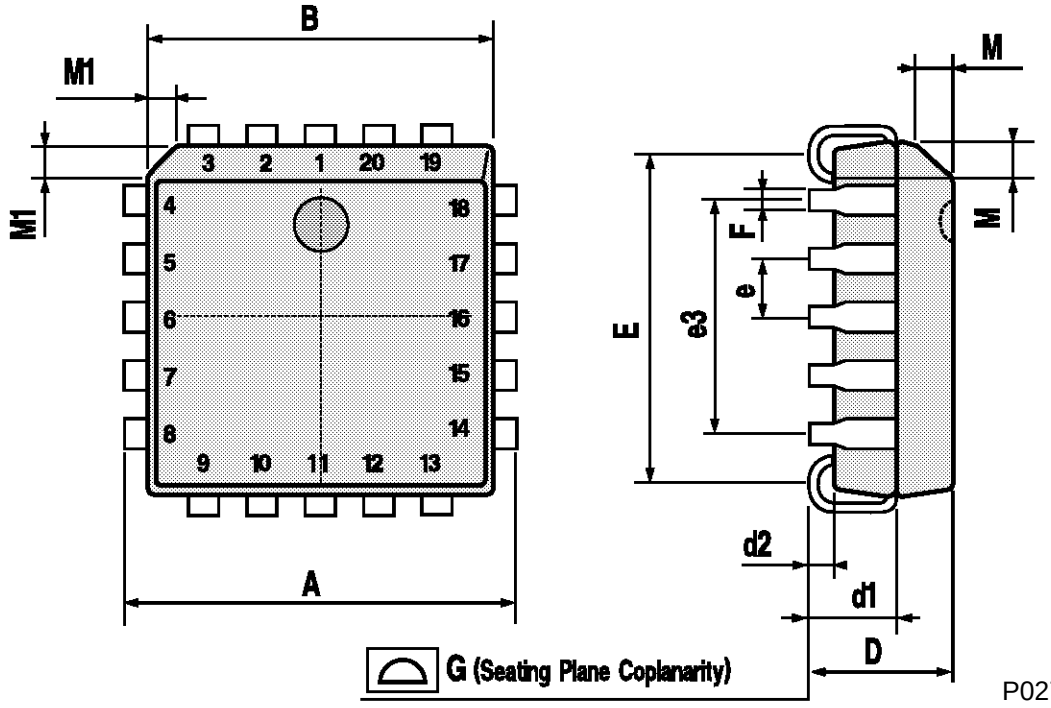
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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